

Comment on "Pinning Strength Dependence of Mixed-State Hall Effect in $\text{YBa}_2\text{Cu}_3\text{O}_7$ Crystals with Columnar Defects"

In their Letter, Kang *et al.* [1] report that pinning induced by heavy ion irradiation modifies the mixed-state Hall conductivity σ_{xy} . The purpose of this Comment is to attract the attention to the fact that it is a misleading statement. Over a wide temperature range where pinning is important, σ_{xy} is practically not changed by irradiation [1]. The difference between the data on the Hall conductivity before and after irradiation is actually within the accuracy of the experiment by Kang *et al.* [1].

For the sample irradiated with the matching field $B_\Phi = 2$ T (B_Φ is the field at which the number of vortices matches the number of columnar defects produced by irradiation) there is no observable difference in σ_{xy} before and after irradiation above $T/T_c \approx 0.924$ for $H = 4$ T and above $T/T_c \approx 0.9525$ for $H = 2$ T (Fig. 4) (all figures cited refer to Ref. [1]). On the other hand, pinning sets in at $T/T_c \approx 0.97$ for $H = 4$ T and $T/T_c \approx 0.97$ for $H = 2$ T (Figs. 1 and 2), as seen from the irradiation-induced change in the longitudinal and Hall resistivities, ρ_{xx} and ρ_{xy} , respectively. Therefore, in the temperature range $T/T_c = 0.924-0.95$ for $H = 4$ T and $T/T_c = 0.9525-0.97$ for $H = 2$ T, the effect of pinning on both ρ_{xx} and ρ_{xy} is significant (for instance, the absolute value of ρ_{xy} decreases from 5×10^{-7} Ω cm before irradiation, see Fig. 2, to 4×10^{-9} Ω cm after irradiation, see Figs. 1 and 3, at $T/T_c \approx 0.9525$ for $H = 2$ T, see Figs. 1-3), whereas the Hall conductivity remains the same before and after irradiation.

There is a narrow temperature window where some difference in σ_{xy} before and after irradiation can be seen ($T/T_c \approx 0.921-0.924$ for $H = 4$ T and $T/T_c \approx 0.949-0.9525$ for $H = 2$ T) (Fig. 4). Let us estimate the accuracy in determining the Hall conductivity $\sigma_{xy} = \rho_{xy}/(\rho_{xx}^2 + \rho_{xy}^2)$ at these temper-

atures. Typical scatter of points for ρ_{xy} (Fig. 3) is 3×10^{-9} Ω cm. At $T/T_c \approx 0.921$ for $H = 4$ T and $T/T_c \approx 0.949$ for $H = 2$ T, the longitudinal resistivity (Fig. 1) drops below 2% of its normal state value ≈ 70 $\mu\Omega$ cm (Fig. 3), i.e., 1.4 $\mu\Omega$ cm. The accuracy in σ_{xy} is $\Delta\sigma_{xy} \approx 3 \times 10^{-9}/(1.4 \times 10^{-6})^2$ (Ω cm) $^{-1} \approx 1.5 \times 10^3$ (Ω cm) $^{-1}$, which is larger or comparable to the difference in the Hall conductivity before and after irradiation (Fig. 4).

Thus, the paper by Kang *et al.* [1] actually confirms our statement about pinning independence of the mixed-state Hall conductivity σ_{xy} in $\text{Ti}_2\text{Ba}_2\text{CaCu}_2\text{O}_8$, $\text{YBa}_2\text{Cu}_3\text{O}_7$ [2], and $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_8$ [3], in agreement with theory by Vinokur *et al.* [4]. Pinning independence of σ_{xy} has also demonstrated by angular scaling of σ_{xy} in $\text{YBa}_2\text{Cu}_3\text{O}_7$ [5,6], $\text{Ti}_2\text{Ba}_2\text{CaCu}_2\text{O}_8$, $\text{Nd}_{1.85}\text{Ce}_{0.15}\text{CuO}_4$ [6], by high-current measurements in Mo_3Si [6], and by observations of a $1/H$ dependence of the Hall conductivity in $\text{Ti}_2\text{Ba}_2\text{CaCu}_2\text{O}_8$ [7] and in $\text{YBa}_2\text{Cu}_3\text{O}_7$ [5,6]. Related work on the thermomagnetic coefficients has been recently performed in $\text{YBa}_2\text{Cu}_3\text{O}_7$ by Clinton *et al.* [8].

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- [1] W. N. Kang *et al.*, Phys. Rev. Lett. **76**, 2993 (1996).
- [2] A. V. Samoilov *et al.*, Phys. Rev. Lett. **74**, 2351 (1995).
- [3] A. V. Samoilov, Phys. Rev. Lett. **71**, 617 (1993).
- [4] V. M. Vinokur *et al.*, Phys. Rev. Lett. **71**, 1242 (1993).
- [5] J. M. Harris, N. P. Ong, and Y. F. Yan, Phys. Rev. Lett. **73**, 610 (1994).
- [6] T. W. Clinton *et al.*, Phys. Rev. B **52**, R7046 (1995).
- [7] A. V. Samoilov *et al.*, Phys. Rev. B **49**, 3667 (1994).
- [8] T. W. Clinton *et al.* (unpublished).